

**SEMISTOP® 4**

## IGBT Module

**SK100MLI066T**

Preliminary Data

### Features

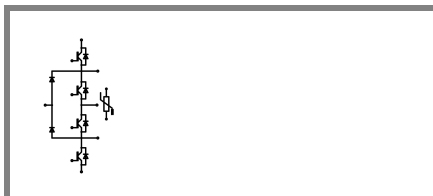
- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded aluminium oxide ceramic (DCB)
- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

### Typical Applications\*

- Multi level inverter

### Remarks

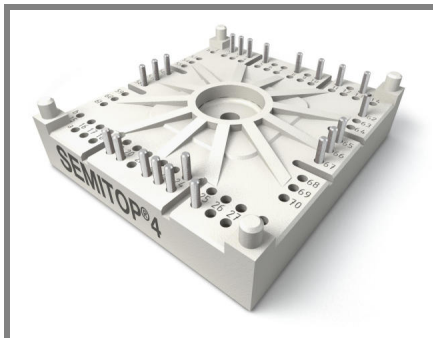
- $V_{isol} = 3000V$  AC, 1s, 50Hz
- Dynamic measure: DUT= IGBT (Gate pin 55) and Neutral Clamp Diode (Kathode pin 56) as free-wheeling diode



**MLI-T**

Absolute Maximum Ratings		$T_s = 25\text{ °C}$ , unless otherwise specified		
Symbol	Conditions	Values		Units
<b>IGBT</b>				
$V_{CES}$	$T_j = 25\text{ °C}$	600		V
$I_C$	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$	105	A
		$T_s = 70\text{ °C}$	80	A
$I_{CRM}$	$I_{CRM} = 2 \times I_{Cnom}$	200		A
$V_{GES}$		± 20		V
$t_{psc}$	$V_{CC} = 360\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125\text{ °C}$ $V_{CES} < 600\text{ V}$	6		µs
<b>Inverse Diode</b>				
$I_F$	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$	110	A
		$T_s = 70\text{ °C}$	85	A
$I_{FRM}$	$I_{FRM} = 2 \times I_{Fnom}$	200		A
<b>Freewheeling Diode</b>				
$I_F$	$T_j = 175\text{ °C}$	$T_s = 25\text{ °C}$	110	A
		$T_s = 70\text{ °C}$	85	A
$I_{FRM}$	$I_{FRM} = 2 \times I_{Fnom}$	200		A
<b>Module</b>				
$I_{t(RMS)}$				A
$T_{vj}$		-40 ... +175		°C
$T_{stg}$		-40 ... +125		°C
$V_{isol}$	AC, 1 min.	2500		V

Characteristics		$T_s = 25\text{ °C}$ , unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units
<b>IGBT</b>					
$V_{GE(th)}$	$V_{GE} = V_{CE}, I_C = 1,6\text{ mA}$	5	5,8	6,5	V
$I_{CES}$	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$	$T_j = 25\text{ °C}$	0,0052		mA
		$T_j = 125\text{ °C}$			mA
$I_{GES}$	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}$			1200	nA
$V_{CE0}$		$T_j = 25\text{ °C}$	0,8	1,1	V
		$T_j = 150\text{ °C}$	0,7	1	V
$r_{CE}$	$V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}$	6,5	8	mΩ
		$T_j = 150\text{ °C}$	9,5	10,5	mΩ
$V_{CE(sat)}$	$I_{Cnom} = 100\text{ A}, V_{GE} = 15\text{ V}$	$T_j = 25\text{ °C}_{chiplev.}$	1,45	1,85	V
		$T_j = 150\text{ °C}_{chiplev.}$	1,65	2,05	V
$C_{ies}$	$V_{CE} = 25, V_{GE} = 0\text{ V}$	$f = 1\text{ MHz}$	6,28		nF
$C_{oes}$			0,4		nF
$C_{res}$			0,19		nF
$Q_G$	$V_{GE} = -7V...+15V$		1000		nC
$t_{d(on)}$	$R_{Gon} = 4\text{ }\Omega$ $di/dt = 3100\text{ A}/\mu\text{s}$	$V_{CC} = 300V$ $I_C = 100A$	136		ns
$t_r$			48		ns
$E_{on}$			2,5		mJ
$t_{d(off)}$	$R_{Goff} = 4\text{ }\Omega$ $di/dt = 3100\text{ A}/\mu\text{s}$	$T_j = 150\text{ °C}$ $V_{GE} = -7/+15V$	457		ns
$t_f$			50		ns
$E_{off}$			4,2		mJ
$R_{th(j-s)}$	per IGBT		0,65		K/W



**SEMITOP® 4**

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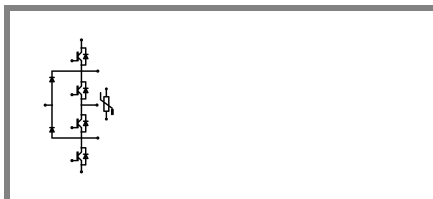
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- One screw mounting
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### Typical Applications\*

- Multi level inverter

### Remarks

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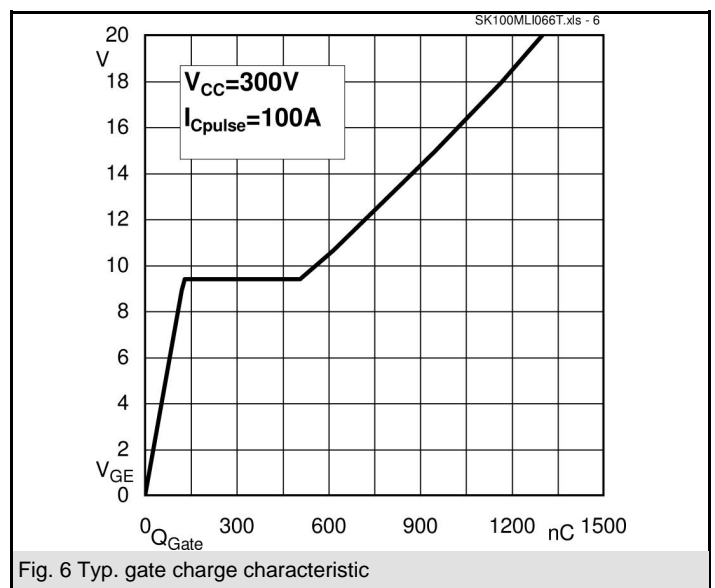
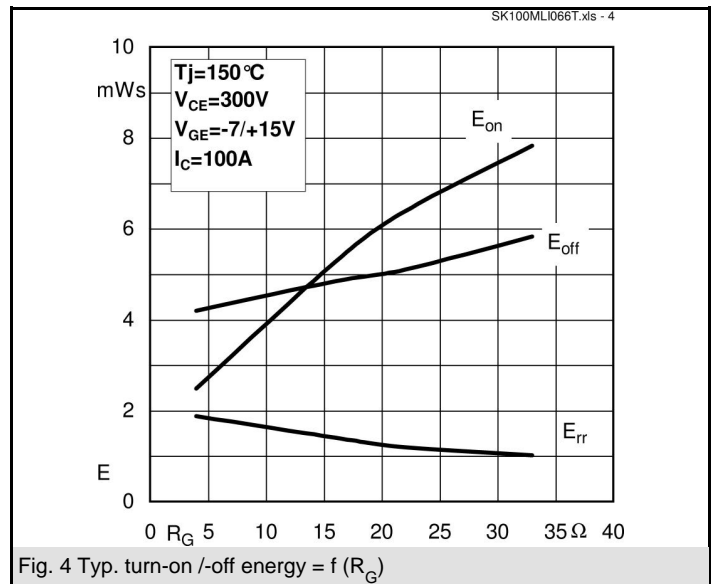
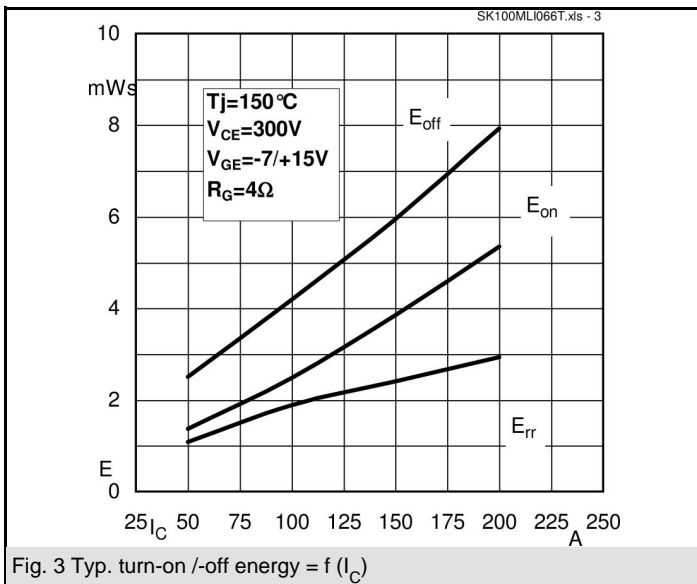
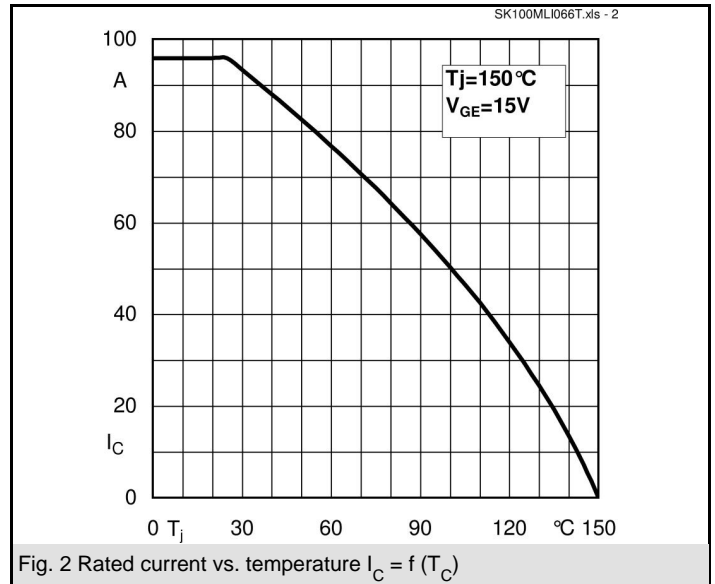
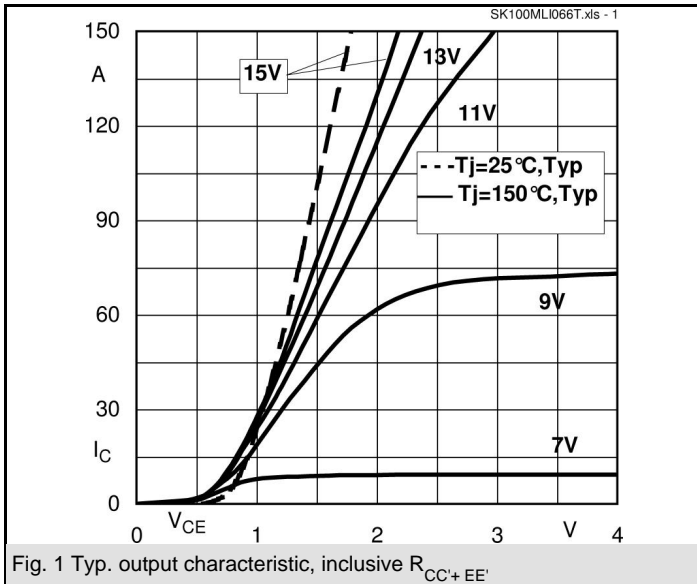


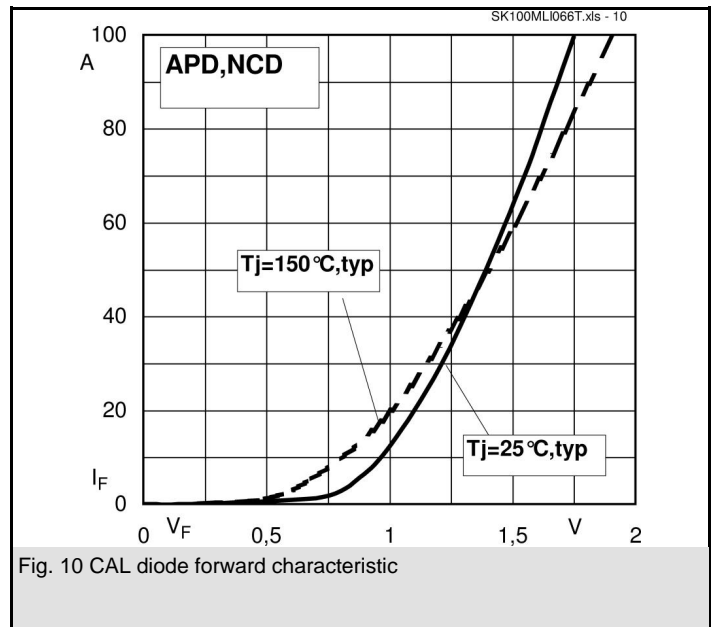
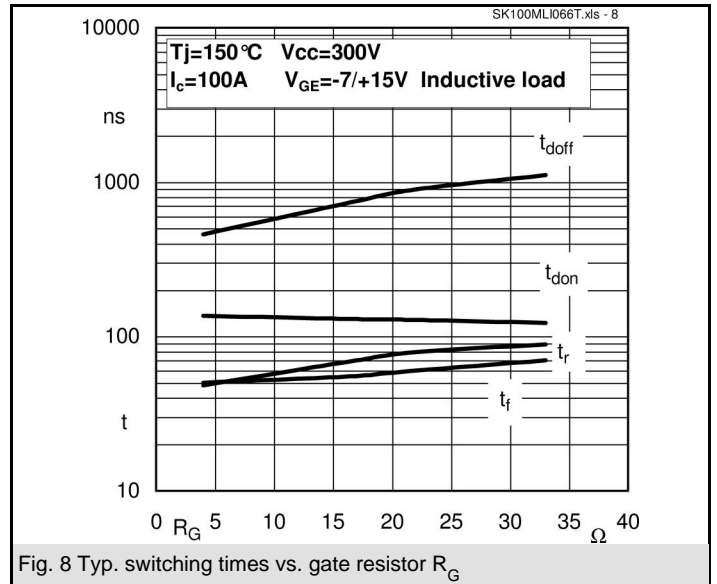
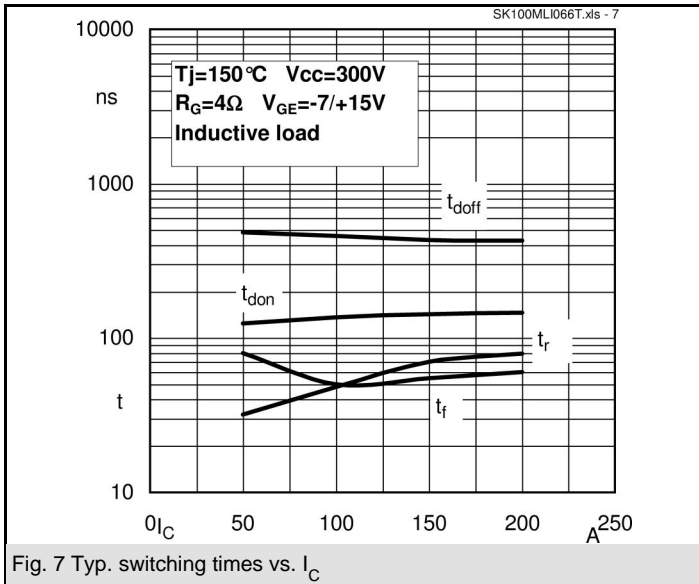
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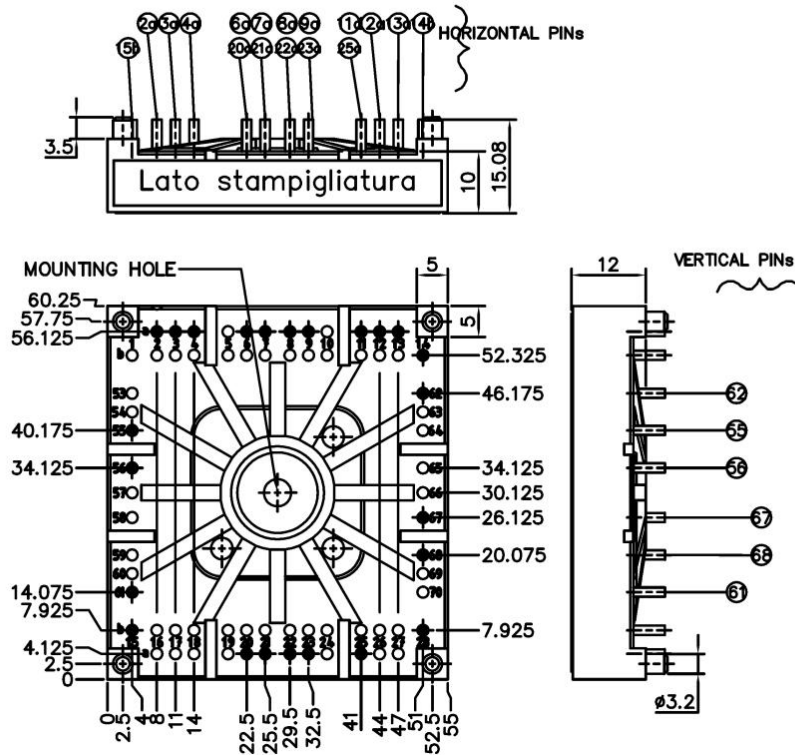
Characteristics					
Symbol	Conditions	min.	typ.	max.	Units
<b>Inverse Diode</b>					
$V_F = V_{EC}$	$I_{Fnom} = 100 A; V_{GE} = 0 V$		$T_j = 25\text{ }^\circ\text{C}_{chiplev.}$	1,35	V
			$T_j = 150\text{ }^\circ\text{C}_{chiplev.}$	1,31	V
$V_{F0}$			$T_j = 25\text{ }^\circ\text{C}$	0,9	V
			$T_j = 150\text{ }^\circ\text{C}$	0,85	V
$r_F$			$T_j = 25\text{ }^\circ\text{C}$	4,5	mΩ
			$T_j = 150\text{ }^\circ\text{C}$	6,3	mΩ
$I_{RRM}$	$I_F = 100 A$		$T_j = 150\text{ }^\circ\text{C}$	84	A
$Q_{rr}$	$di/dt = 3100 A/\mu s$			6	μC
$E_{rr}$	$V_R = 300V$			1,9	mJ
$R_{th(j-s)D}$	per diode			0,9	K/W
<b>Freewheeling Diode (Neutral Clamp Diode)</b>					
$V_F = V_{EC}$	$I_{Fnom} = 100 A; V_{GE} = 0 V$		$T_j = 25\text{ }^\circ\text{C}_{chiplev.}$	1,35	V
			$T_j = 150\text{ }^\circ\text{C}_{chiplev.}$	1,31	V
$V_{F0}$			$T_j = 25\text{ }^\circ\text{C}$	0,9	V
			$T_j = 150\text{ }^\circ\text{C}$	0,85	V
$r_F$			$T_j = 25\text{ }^\circ\text{C}$	4,5	V
			$T_j = 150\text{ }^\circ\text{C}$	6,3	V
$I_{RRM}$	$I_F = 100 A$		$T_j = 150\text{ }^\circ\text{C}$	80	A
$Q_{rr}$	$di/dt = 3000 A/\mu s$			18	μC
$E_{rr}$	$V_R = 300V$			1,9	mJ
$R_{th(j-s)FD}$	per diode			0,9	K/W
$M_s$	to heat sink		2,5	2,75	Nm
w				60	g
<b>Temperature sensor</b>					
$R_{100}$	$T_s = 100\text{ }^\circ\text{C}$ ( $R_{25} = 5k\Omega$ )			493±5%	Ω

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

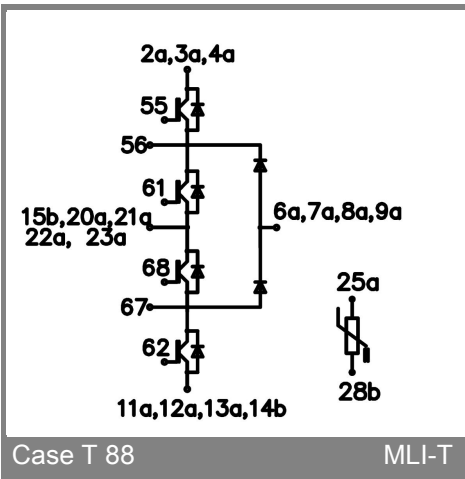
\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.







Case T 88 (Suggested hole diameter for the solder pins in the circuit board: 2mm. Suggested hole diameter for the mounting pins in the circuit board: 3,6mm )



Case T 88

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